



**US2AB-US2MB High Efficient Rectifier**

**Feature**

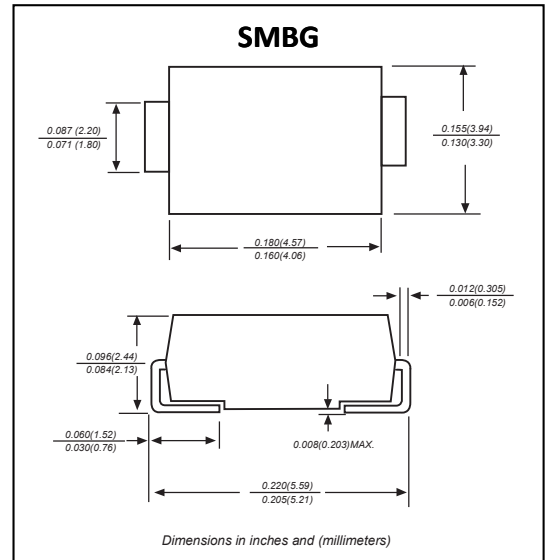
- $I_o$  2A
- $V_{RRM}$  50V-1000V
- Glass passivated chip
- High surge current capability

**Application**

- Rectifier

**Marking**

- US2X X:From A To M



**ABSOLUTE MAXIMUM RATINGS ( $T_a=25^\circ\text{C}$  unless otherwise noted)**

Parameter	Symbo I	US2							Unit
		AB	BB	DB	GB	JB	KB	MB	
Repetitive Peak Reverse Voltage	$V_{RRM}$	50	100	200	400	600	800	1000	V
Maximum RMS Voltage	$V_{RMS}$	35	70	140	280	420	560	700	V
Average Forward Current 60HZ Half-sine wave, Resistance load, $T_L=115^\circ\text{C}$	$I_{F(AV)}$	2							A
Non-repetitive Peak Forward Surge Current 60Hz Half-sine wave ,1 cycle , $T_a =25^\circ\text{C}$	$I_{FSM}$	50							A
Junction Temperature	$T_J$	-55 ~ +150							$^\circ\text{C}$
Storage Temperature	$T_{STG}$	-55 ~ +150							$^\circ\text{C}$

**ELECTRICAL CHARACTERISTICS ( $T_a=25^\circ\text{C}$  unless otherwise noted)**

Parameter	Symbo I	Test Condition	US2						Unit
			AB	BB	DB	GB	JB	KB	
Peak Forward Voltage	$V_F$	$I_F = 1\text{A}$	1.0			1.3	1.7		V
Maximum reverse recovery time	$t_{rr}$	$I_F=0.5\text{A}, I_R=1.0\text{A}, I_{rr}=0.25\text{A}$	50				75		ns
Peak Reverse Current	$I_{RRM1}$	$V_{RM}=V_{RRM}$	$T_a=25^\circ\text{C}$		5				$\mu\text{A}$
	$I_{RRM2}$		$T_a=100^\circ\text{C}$		100				$\mu\text{A}$
Thermal Resistance(Typical)	$R_{\theta J-A}$	Between junction and ambient	80						$^\circ\text{C/W}$
	$R_{\theta J-L}$	Between junction and terminal	20						$^\circ\text{C/W}$

**Typical Characteristics**

FIG.1: FORWARD CURRENT DERATING CURVE

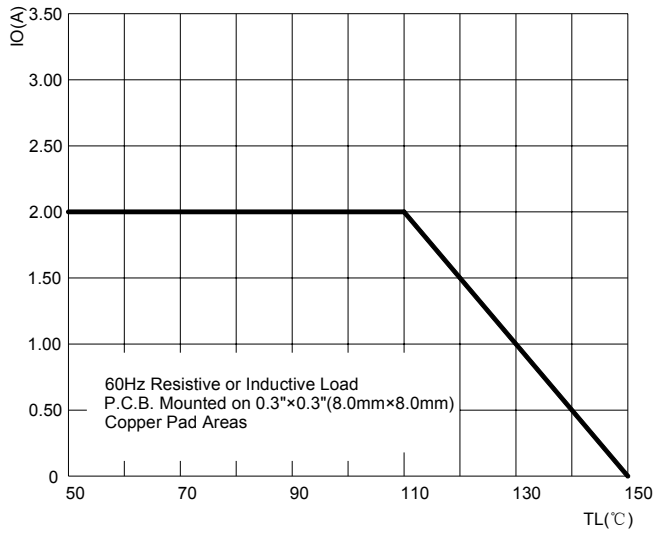


FIG.2: MAXIMUM NON-REPETITIVE FORWARD URGE CURRENT

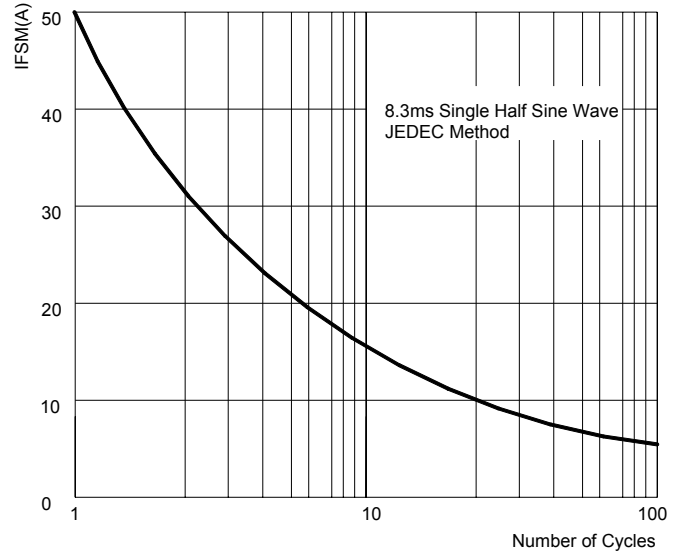


FIG.3: TYPICAL FORWARD CHARACTERISTICS

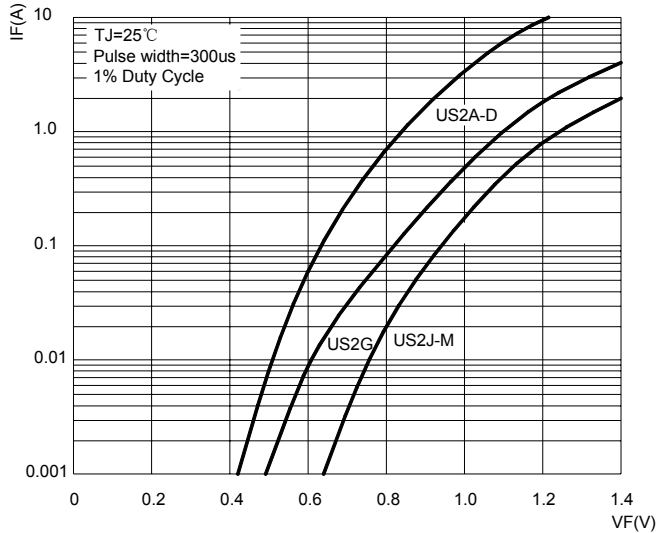


FIG.4: TYPICAL REVERSE CHARACTERISTICS

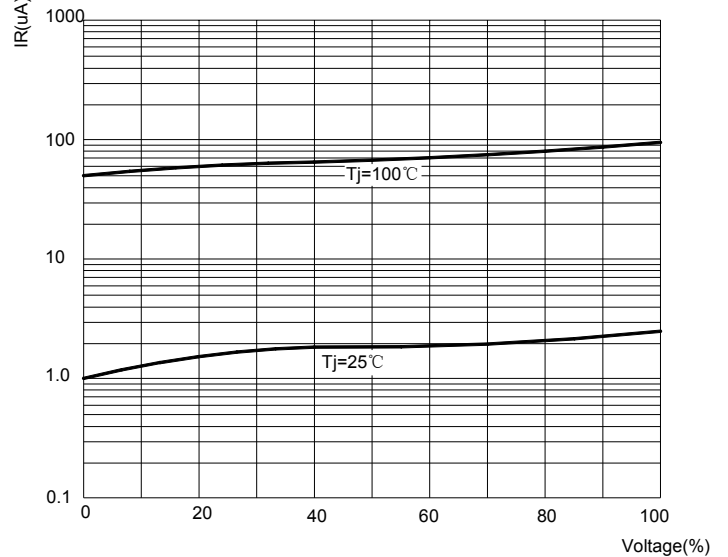
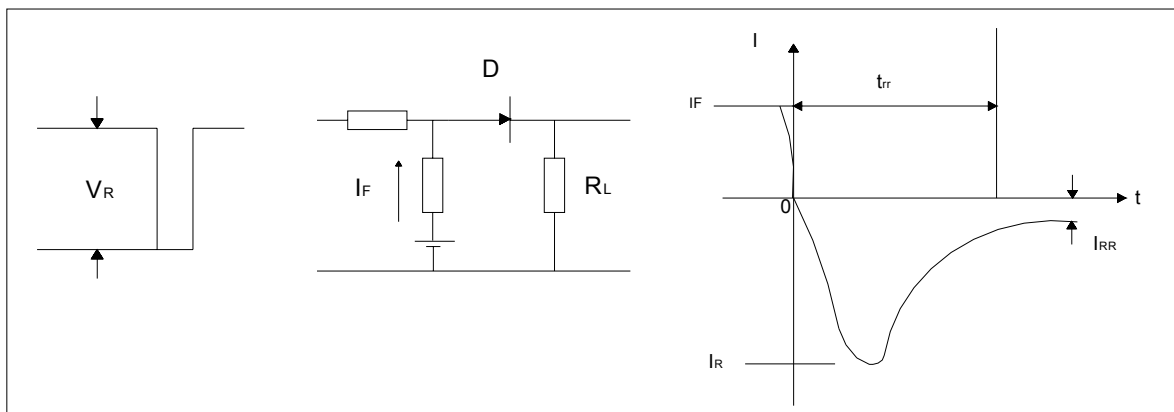


FIG.5: Diagram of circuit and Testing wave form of reverse recovery time



单击下面可查看定价，库存，交付和生命周期等信息

[>>GP\(格瑞宝\)](#)